

# MOSFET

Metal Oxide Semiconductor Field Effect Transistor

## CoolMOS™ C6 600V

600V CoolMOS™ C6 Power Transistor  
IPP60R1K4C6

## Data Sheet

Rev. 2.0  
Final

Industrial & Multimarket

## 1 Description

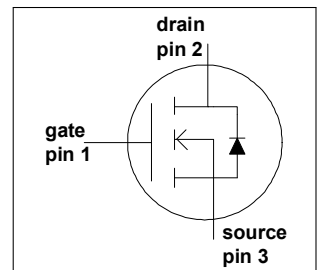
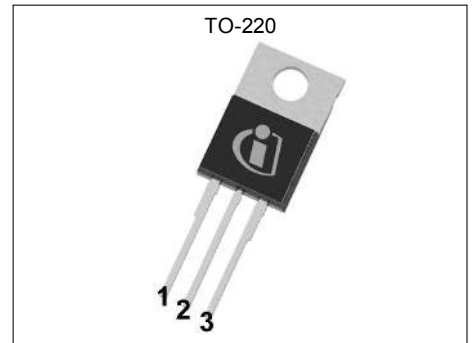
CoolMOS™ is a revolutionary technology for high voltage power MOSFETs, designed according to the superjunction (SJ) principle and pioneered by Infineon Technologies. CoolMOS™ C6 series combines the experience of the leading SJ MOSFET supplier with high class innovation. The resulting devices provide all benefits of a fast switching SJ MOSFET while not sacrificing ease of use. Extremely low switching and conduction losses make switching applications even more efficient, more compact, lighter and cooler.

### Features

- Extremely low losses due to very low FOM  $R_{ds(on)} \cdot Q_g$  and  $E_{oss}$
- Very high commutation ruggedness
- Easy to use/drive
- Pb-free plating, Halogen free mold compound
- Qualified for industrial grade applications according to JEDEC (J-STD20 and JESD22)

### Applications

PFC stages, hard switching PWM stages and resonant switching PWM stages for e.g. PC Silverbox, Adapter, LCD & PDP TV, Lighting, Server, Telecom and UPS.



**Table 1 Key Performance Parameters**

Parameter	Value	Unit
$V_{DS} @ T_{j \max}$	650	V
$R_{DS(on),max}$	1.4	$\Omega$
$Q_g,typ$	9.4	nC
$I_D,pulse$	8	A
$E_{oss} @ 400V$	1	$\mu J$
Body diode $di/dt$	500	A/ $\mu s$

Type / Ordering Code	Package	Marking	Related Links
IPP60R1K4C6	PG-TO 220	6R1K4C6	see Appendix A



**Table of Contents**

Description ..... 2

Table of Contents ..... 3

Maximum ratings ..... 4

Thermal characteristics ..... 5

Electrical characteristics ..... 6

Electrical characteristics diagrams ..... 8

Test Circuits ..... 12

Package Outlines ..... 13

Appendix A ..... 14

Revision History ..... 15

Disclaimer ..... 15

## 2 Maximum ratings

at  $T_j = 25^\circ\text{C}$ , unless otherwise specified

**Table 2 Maximum ratings**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current <sup>1)</sup>	$I_D$			3.2	A	$T_C = 25^\circ\text{C}$
				2.0		$T_C = 100^\circ\text{C}$
Pulsed drain current <sup>2)</sup>	$I_{D,pulse}$			8	A	$T_C = 25^\circ\text{C}$
Avalanche energy, single pulse	$E_{AS}$			26	mJ	$I_D = 0.6\text{A}$ , $V_{DD} = 50\text{V}$ (see table 18)
Avalanche energy, repetitive	$E_{AR}$			0.09	mJ	$I_D = 0.6\text{A}$ , $V_{DD} = 50\text{V}$
Avalanche current, repetitive	$I_{AR}$			0.6	A	
MOSFET dv/dt ruggedness	dv/dt			50	V/ns	$V_{DS} = 0 \dots 480\text{V}$
Gate source voltage	$V_{GS}$	-20		20	V	static
		-30		30		AC ( $f > 1\text{ Hz}$ )
Power dissipation (non FullPAK) TO-220	$P_{Tot}$			28.4	W	$T_C = 25^\circ\text{C}$
Operating and storage temperature	$T_j, T_{stg}$	-55		150	$^\circ\text{C}$	
Mounting torque (non FullPAK) TO-220				60	Ncm	M3 and M3.5 screws
Continuous diode forward current	$I_S$			2.8	A	$T_C = 25^\circ\text{C}$
Diode pulse current	$I_{S,pulse}$			8	A	$T_C = 25^\circ\text{C}$
Reverse diode dv/dt <sup>3)</sup>	dv/dt			15	V/ns	$V_{DS} = 0 \dots 480\text{V}$ , $I_{SD} \leq I_D$ , $T_j = 25^\circ\text{C}$ (see table 16)
Maximum diode commutation speed	$di_f/dt$			500	A/ $\mu\text{s}$	

<sup>1)</sup> Limited by  $T_{j \max}$ . Maximum duty cycle  $D=0.75$

<sup>2)</sup> Pulse width  $t_p$  limited by  $T_{j \max}$

<sup>3)</sup> Identical low side and high side switch with identical  $R_G$

### 3 Thermal characteristics

**Table 3 Thermal characteristics TO-220**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	$R_{thJC}$			4.4	°C/W	
Thermal resistance, junction - ambient	$R_{thJA}$			62	°C/W	leaded
Soldering temperature, wavesoldering only allowed at leads	$T_{sold}$			260	°C	1.6 mm (0.063 in.) from case for 10s

## 4 Electrical characteristics

 at  $T_j = 25^\circ\text{C}$ , unless otherwise specified

**Table 4 Static characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	600			V	$V_{GS} = 0V, I_D = 0.25mA$
Gate threshold voltage	$V_{GS(th)}$	2.5	3	3.5	V	$V_{DS} = V_{GS}, I_D = 0.09mA$
Zero gate voltage drain current	$I_{DSS}$			1	$\mu A$	$V_{DS} = 600V, V_{GS} = 0V, T_j = 25^\circ C$
			10			$V_{DS} = 600V, V_{GS} = 0V, T_j = 150^\circ C$
Gate-source leakage current	$I_{GSS}$			100	nA	$V_{GS} = 20V, V_{DS} = 0V$
Drain-source on-state resistance	$R_{DS(on)}$		1.260	1.4	$\Omega$	$V_{GS} = 10V, I_D = 1.1A, T_j = 25^\circ C$
			3.280			$V_{GS} = 10V, I_D = 1.1A, T_j = 150^\circ C$
Gate resistance	$R_G$		14		$\Omega$	$f = 1MHz, \text{open drain}$

**Table 5 Dynamic characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance	$C_{iss}$		200		pF	$V_{GS} = 0V, V_{DS} = 100V, f = 1MHz$
Output capacitance	$C_{oss}$		16		pF	
Effective output capacitance, energy related <sup>1)</sup>	$C_{o(er)}$		11		pF	$V_{GS} = 0V, V_{DS} = 0 \dots 480V$
Effective output capacitance, time related <sup>2)</sup>	$C_{o(tr)}$		41.3		pF	$I_D = \text{constant}, V_{GS} = 0V, V_{DS} = 0 \dots 480V$
Turn-on delay time	$t_{d(on)}$		8		ns	$V_{DD} = 480V, V_{GS} = 10V, I_D = 1.4A, R_G = 12.2\Omega$ (see table 17)
Rise time	$t_r$		7		ns	
Turn-off delay time	$t_{d(off)}$		40		ns	
Fall time	$t_f$		20		ns	

**Table 6 Gate charge characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	$Q_{gs}$		1.1		nC	$V_{DD} = 480V, I_D = 1.4A, V_{GS} = 0 \text{ to } 10V$
Gate to drain charge	$Q_{gd}$		5		nC	
Gate charge total	$Q_g$		9.4		nC	
Gate plateau voltage	$V_{plateau}$		5.4		V	

<sup>1)</sup>  $C_{o(er)}$  is a fixed capacitance that gives the same stored energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{(BR)DSS}$ 
<sup>2)</sup>  $C_{o(tr)}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{(BR)DSS}$

**Table 7 Reverse diode characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode forward voltage	$V_{SD}$		0.9		V	$V_{GS} = 0V, I_F = 1.4A, T_j = 25^\circ C$
Reverse recovery time	$t_{rr}$		230		ns	$V_R = 400V, I_F = 1.4A,$ $di_F/dt = 100A/\mu s$ (see table 16)
Reverse recovery charge	$Q_{rr}$		1.1		$\mu C$	
Peak reverse recovery current	$I_{rrm}$		9.8		A	

### 5 Electrical characteristics diagrams

Table 8

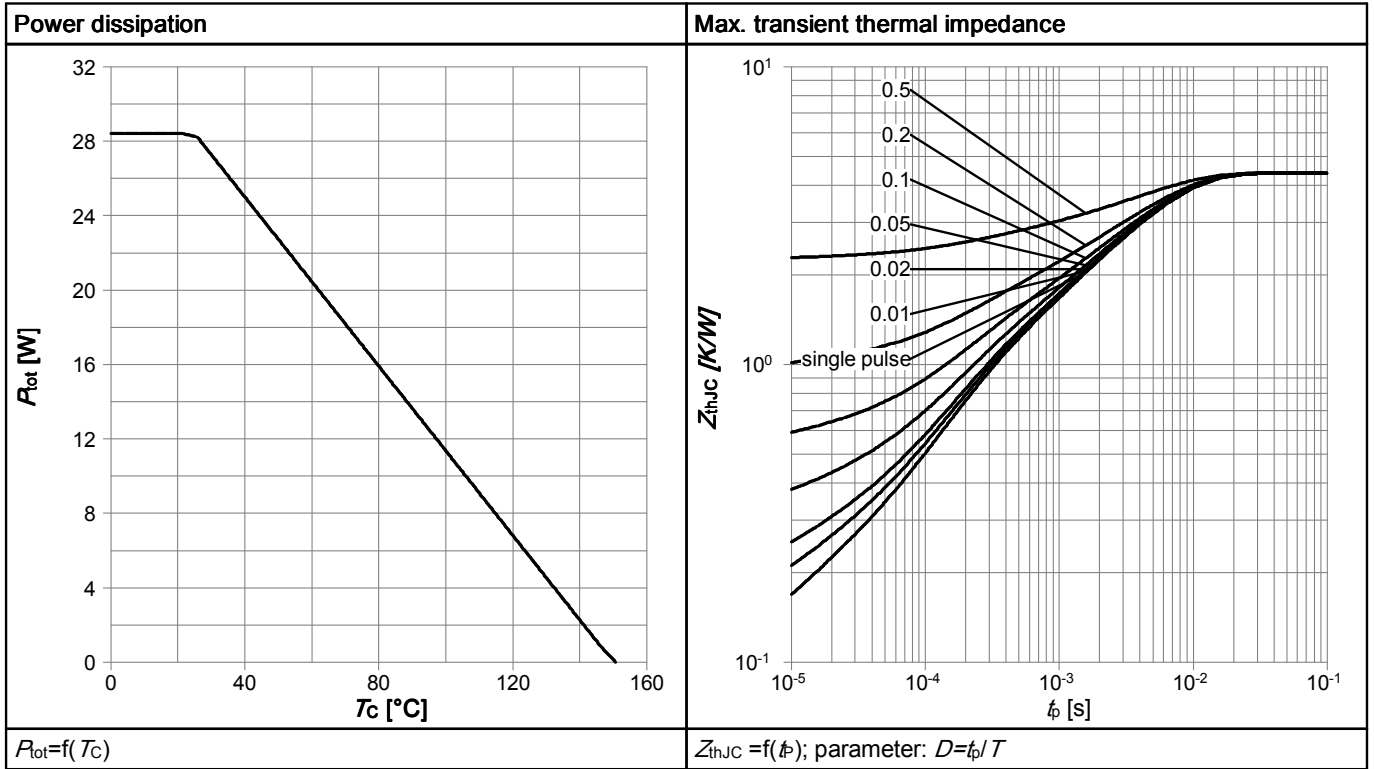


Table 9

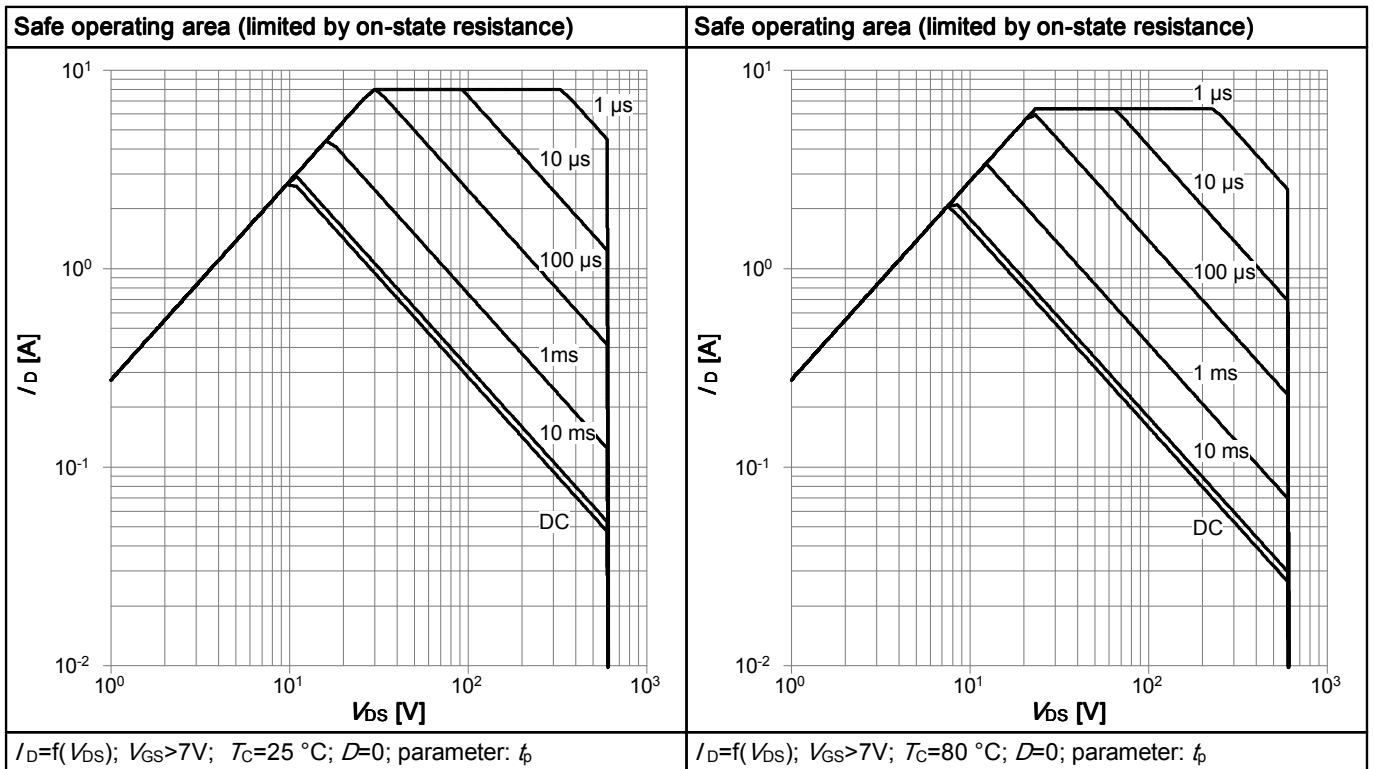




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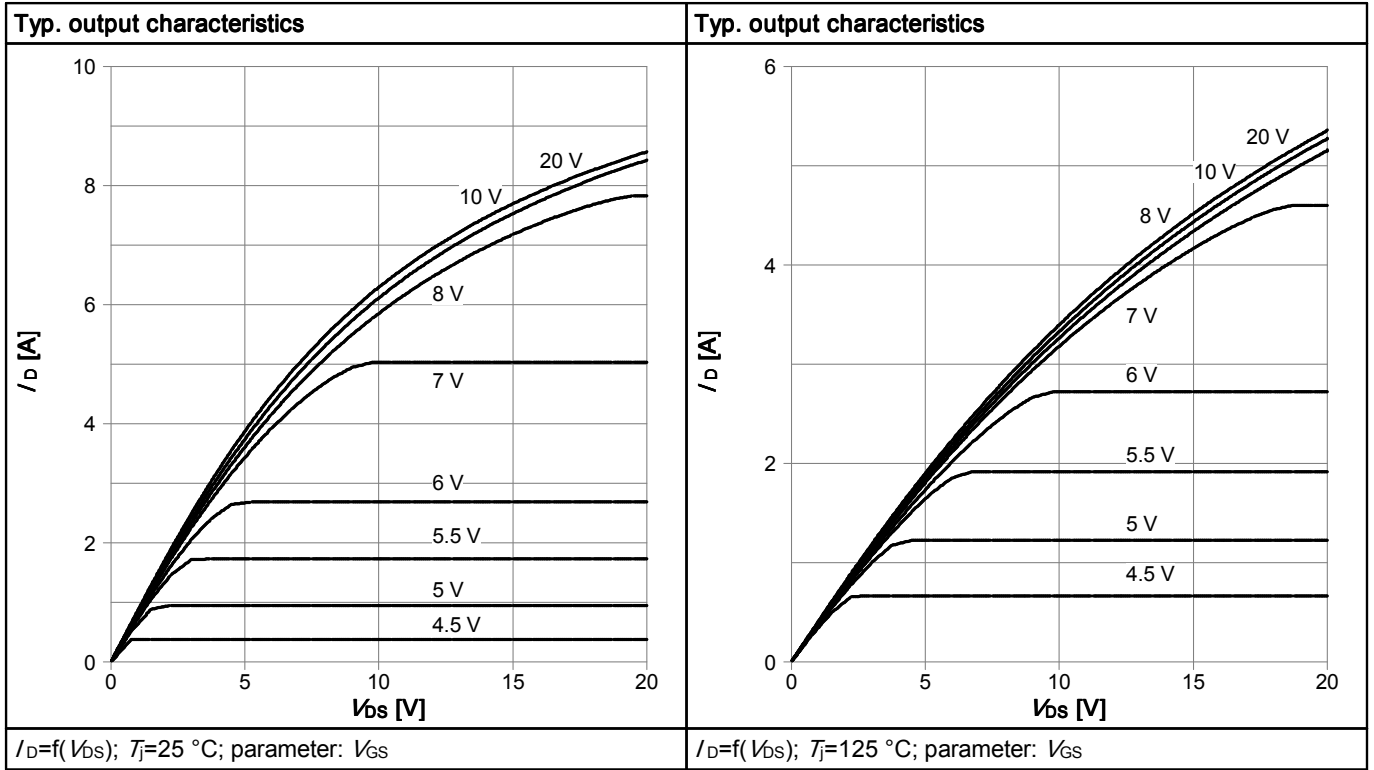


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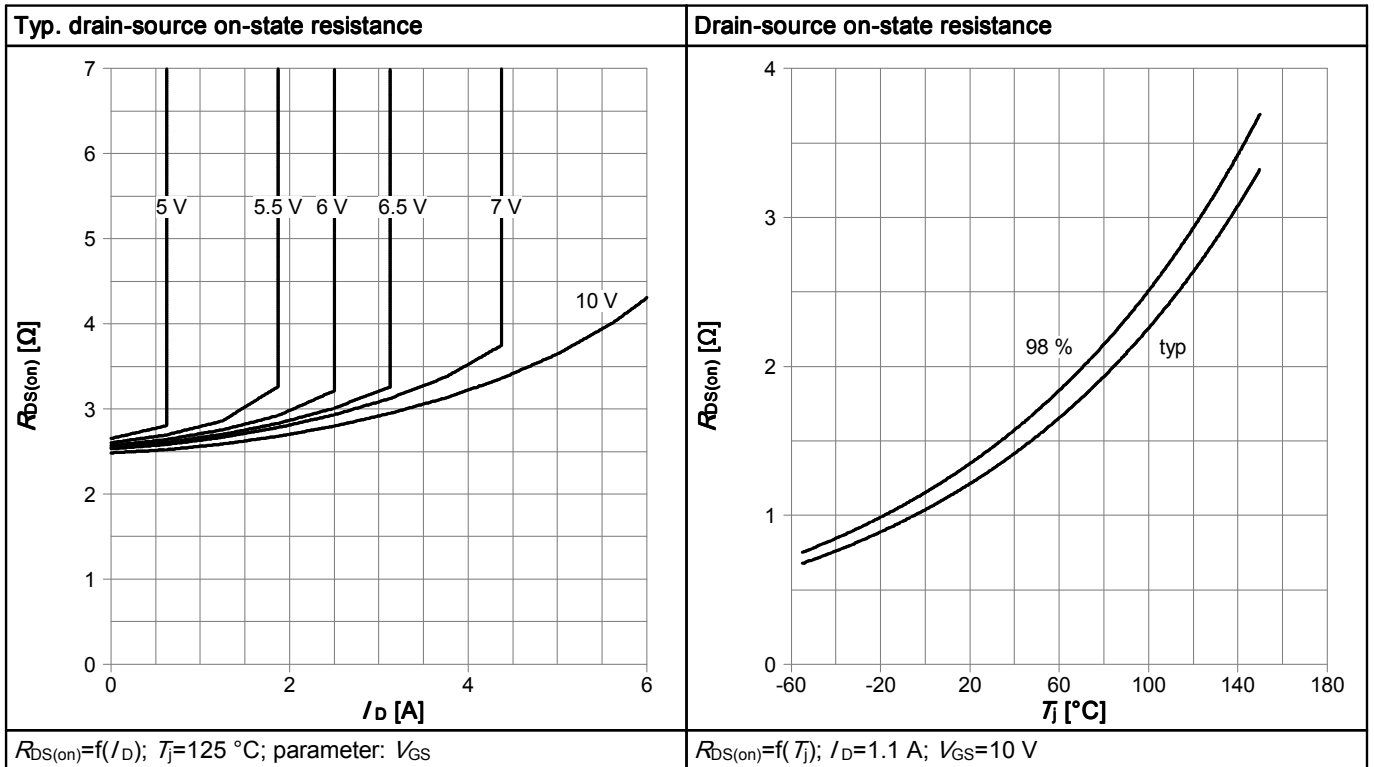


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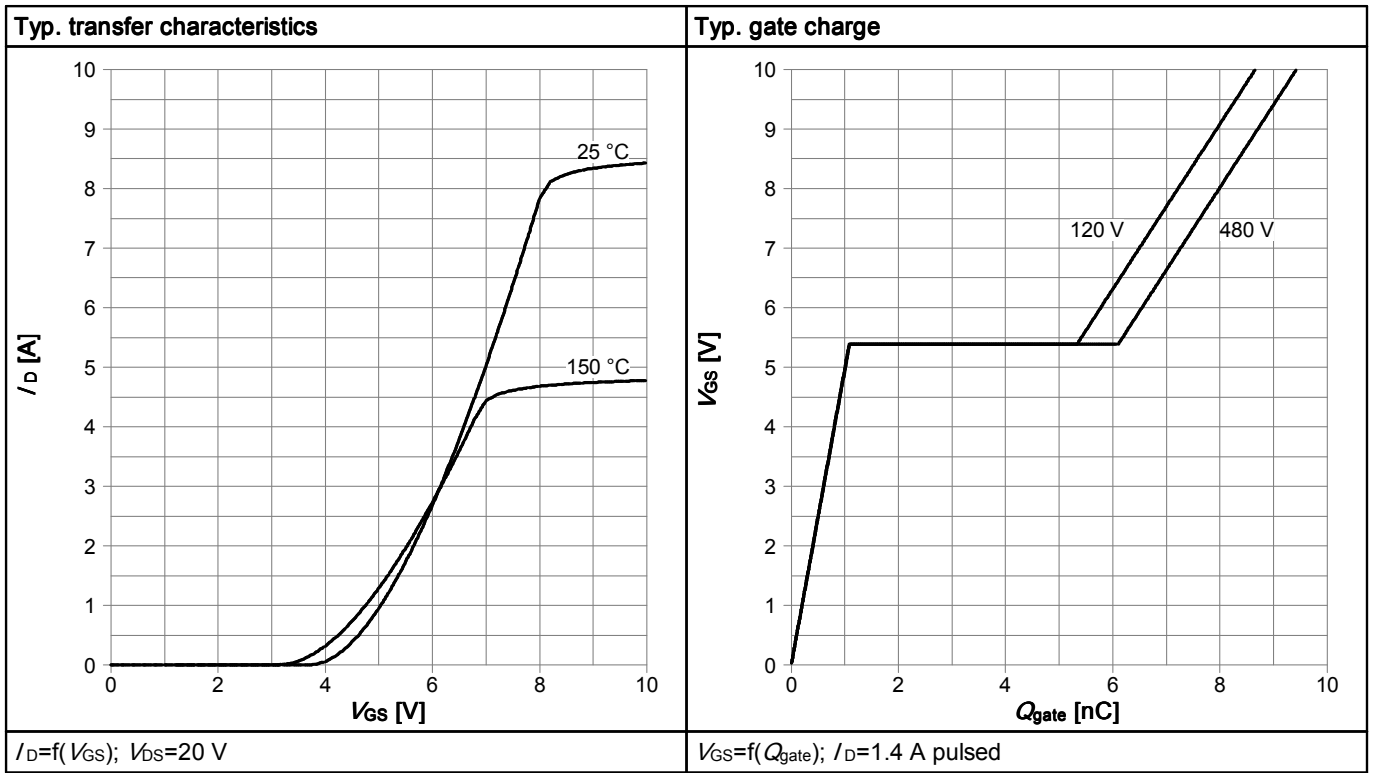


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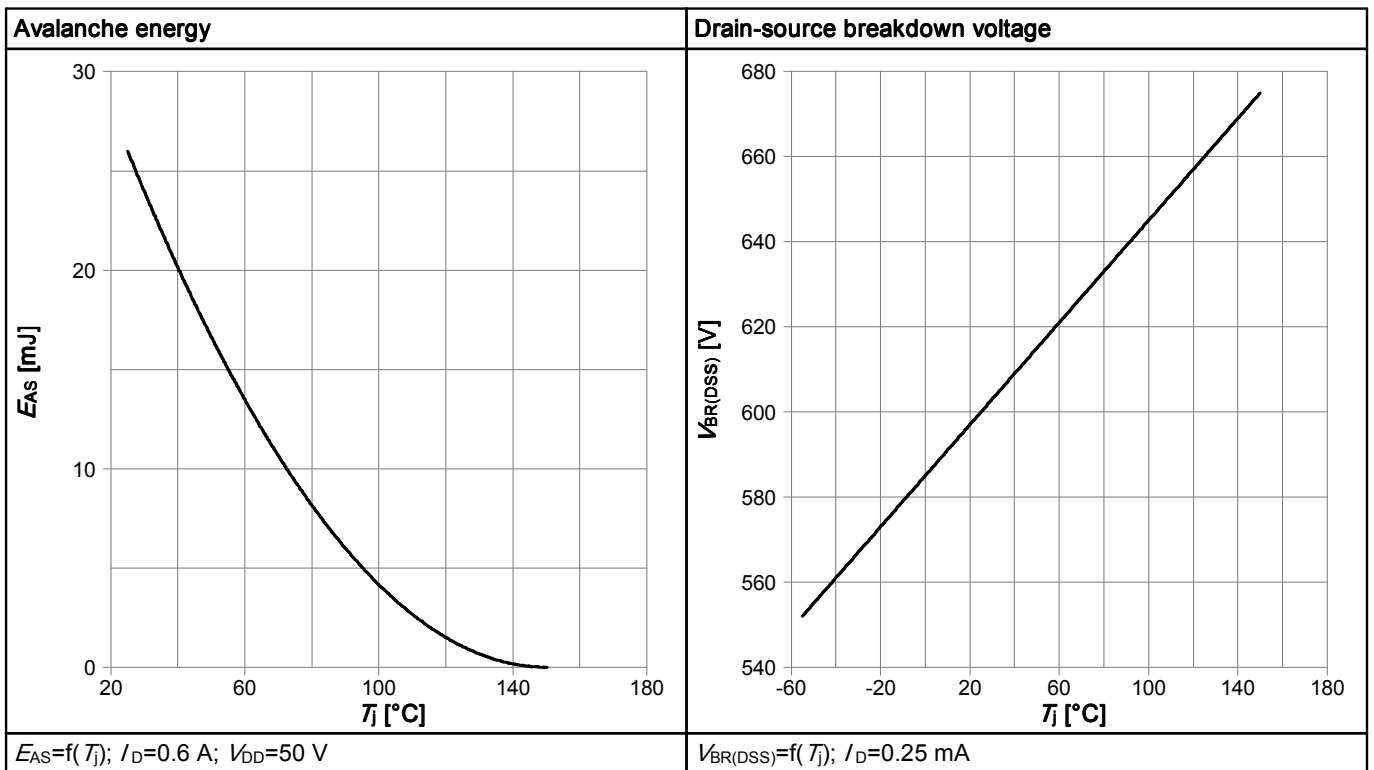


Table 14

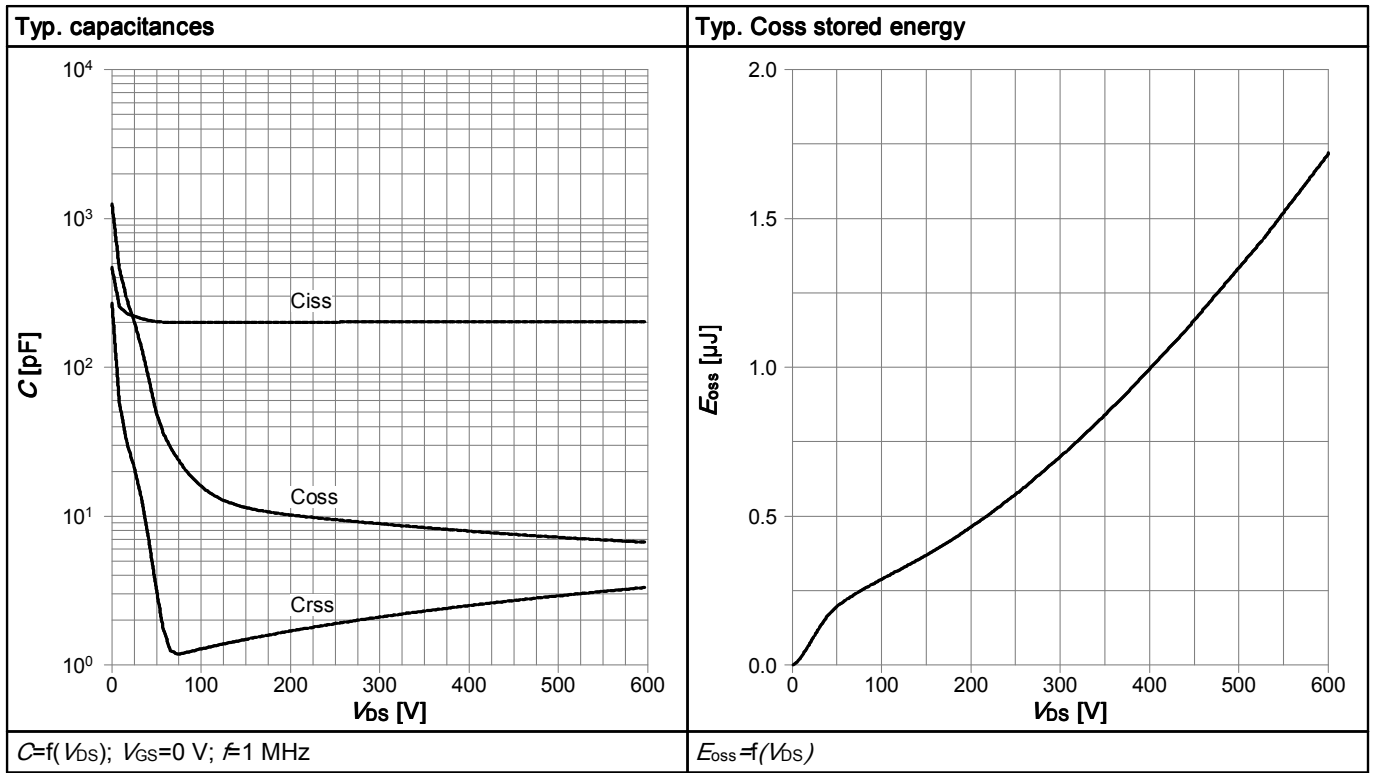
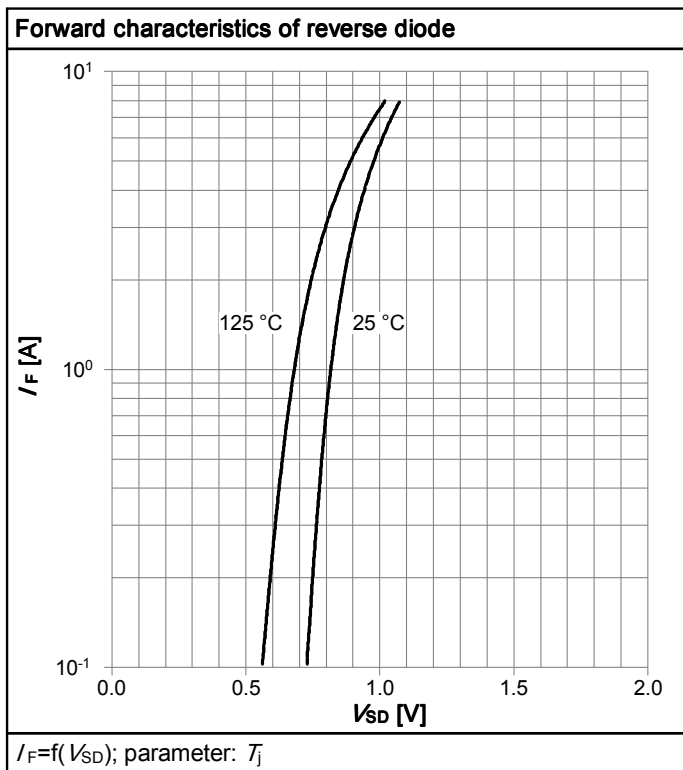
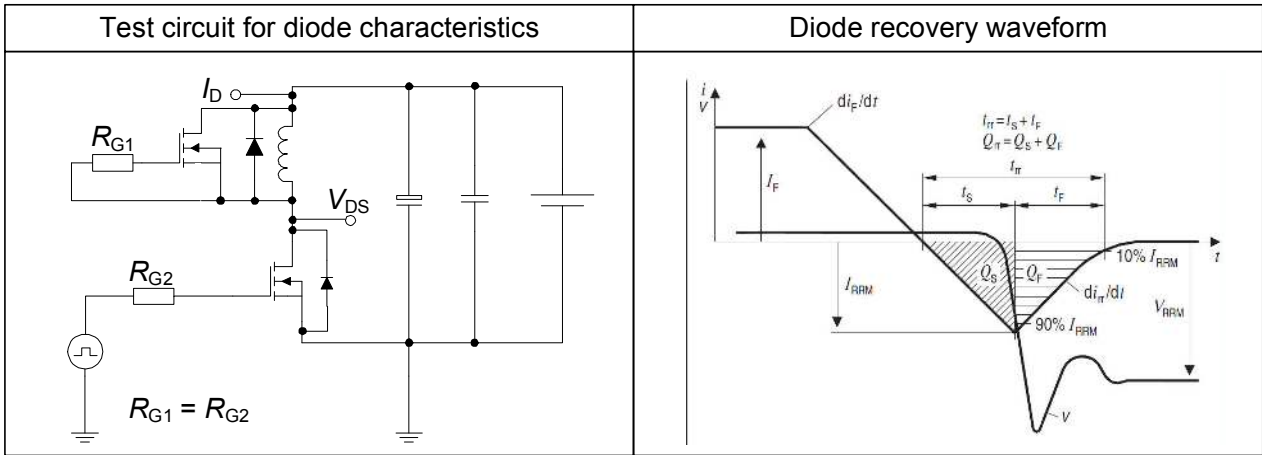


Table 15

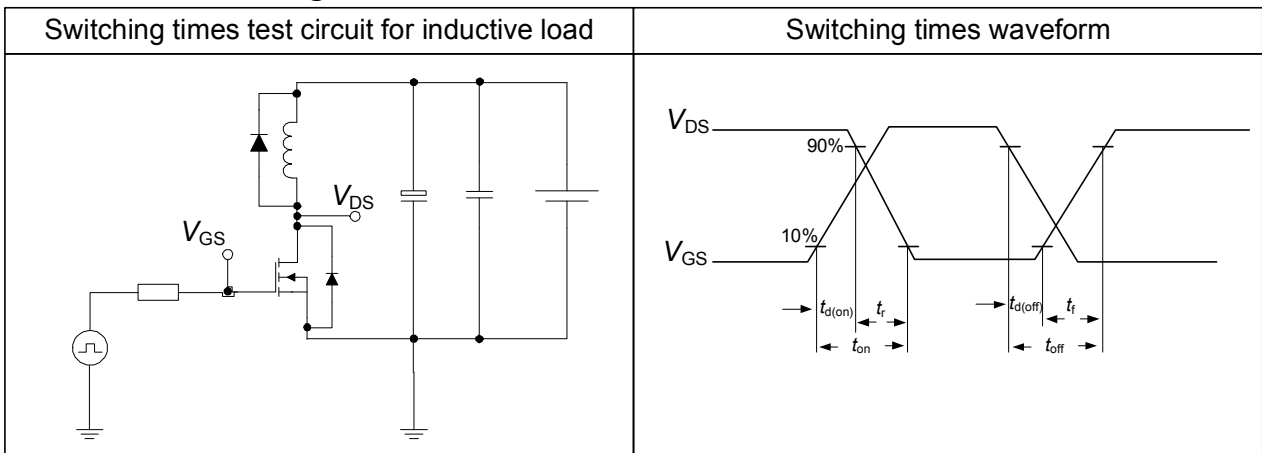


## 6 Test Circuits

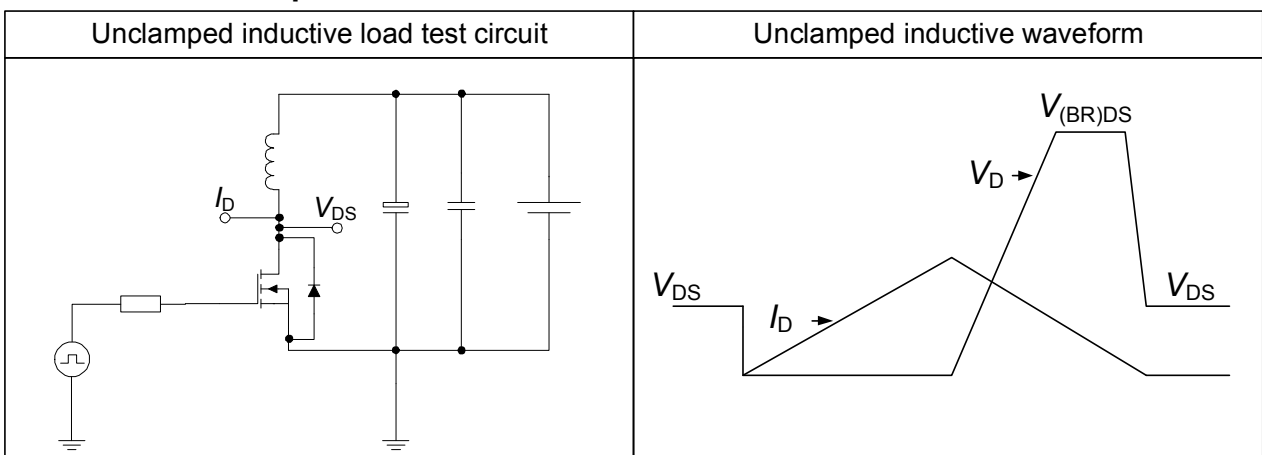
**Table 16 Diode characteristics**



**Table 17 Switching times**



**Table 18 Unclamped inductive**



7 Package Outlines

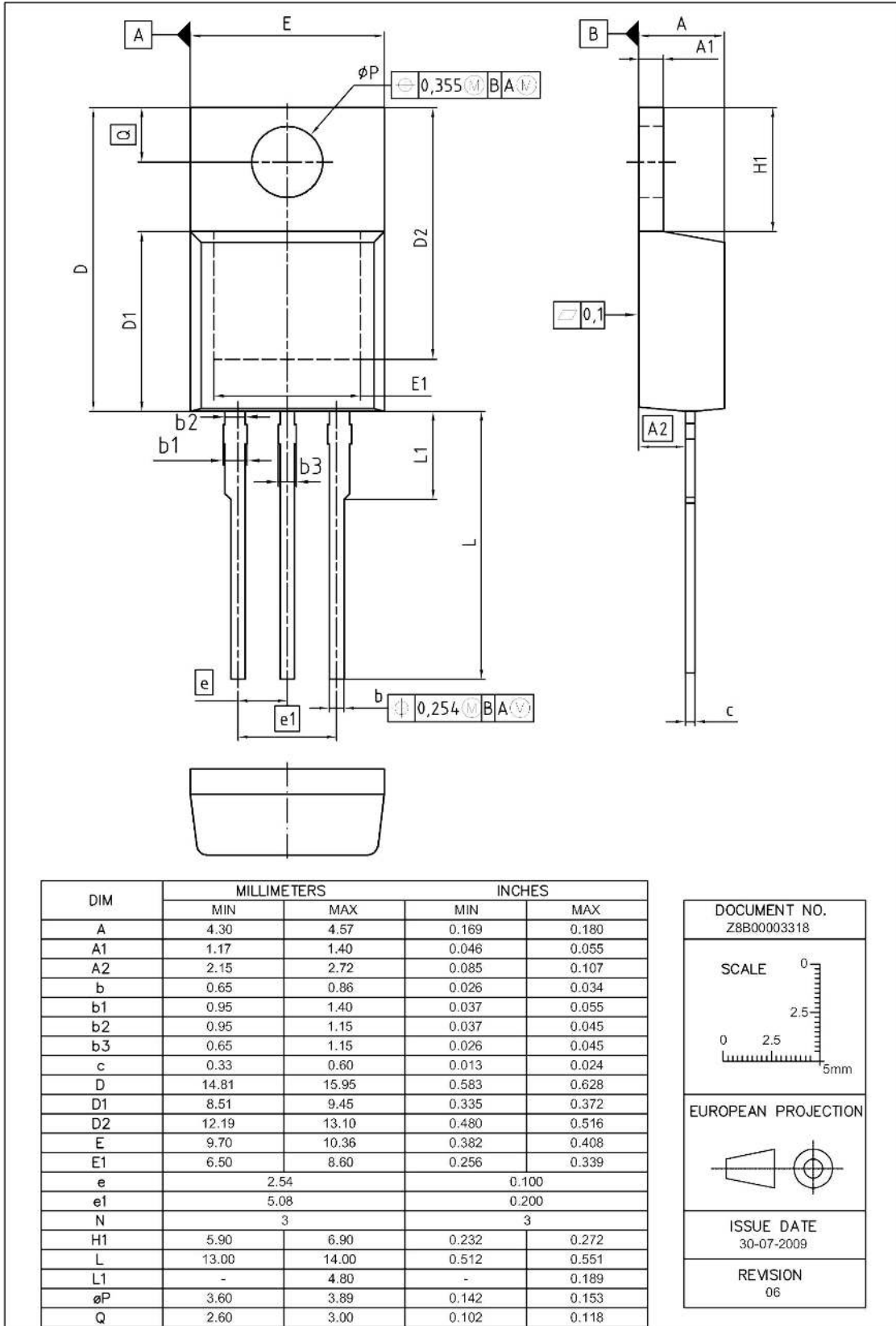


Figure 1 Outline PG-TO 220, dimensions in mm/inches

## 8 Appendix A

### Table 19 Related Links

- **IFX C6 Product Brief:**

<http://www.infineon.com/dgdl/Product+Brief+600V+CoolMOS+C6+.pdf?folderId=db3a3043156fd5730115939eb6b506db>

- **IFX C6 Portfolio:**

[http://www.infineon.com/cms/en/product/findProductTypeByName.html?q=ip\\*c6](http://www.infineon.com/cms/en/product/findProductTypeByName.html?q=ip*c6)

- **IFX CoolMOS Webpage:**

<http://www.infineon.com/cms/en/product/channel.html?channel=ff80808112ab681d0112ab6a628704d8>

- **IFX Design Tools:**

<http://www.infineon.com/cms/en/product/promopages/designtools/index.html>

## Revision History

IPP60R1K4C6

**Revision: 2012-02-02, Rev. 2.0**

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.0	2012-02-02	Final datasheet release

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### Edition 2011-08-01

#### Published by

**Infineon Technologies AG**

**81726 München, Germany**

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